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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Application Number		10729831
	Filing Date		2003-12-05
	First Named Inventor	En-Hsing Chen	
	Art Unit	2827	
	Examiner Name	Ly D. Pham	
	Attorney Docket Number	023-0028	

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Examiner Initial*	Cite No	Patent Number	Kind Code ¹	Issue Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines where Relevant Passages or Relevant Figures Appear
LP	1	5621684		1997-04-15	Jung	
	2	5682350		1997-10-28	Lee, et al.	
	3	5729491		1998-03-17	Kim et al.	
	4	6118696		2000-09-12	Choi	
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	7	6301155		2001-10-09	Fujiwara	
↓	8	6373095		2002-04-16	Bracchitta et al.	

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LP	9	6584006		2003-06-24	Viehmman	
	10	6614070		2003-09-02	Hirose et al.	
	11	6747899		2004-06-08	Hsia et al.	
	12	6765813		2004-07-20	Scheuerlein et al.	
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	14	6982902		2006-01-03	Gogl et al.	
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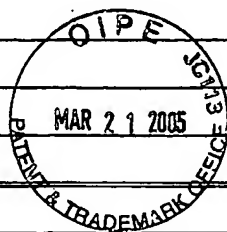
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PTO/SB/08A (Substitute for form 1449/PTO)		Attorney Docket No.: 023-0028
		Application No.: 10/729,831
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		First Named Inventor: En-Hsing Chen et al.
		Filing Date: December 5, 2003
		Group Art Unit: 2827
		Examiner Name: Ly Duy Pham
Sheet 1 of 5		Date Submitted: March 15, 2005



U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
LP	AA	4,142,176	02-27-1979	Dozier		
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	AP	JA-2001-358237	12-26-2001			
↓	AQ	JA-2002-280467	09-27-2002			
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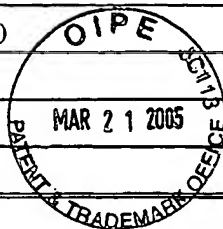
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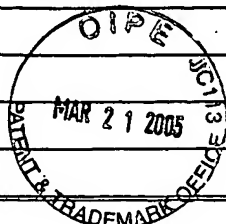


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	BE					
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LP	BZ	6,515,888	02-04-2003	Johnson et al.	
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	CM					
	CN					
	CO					
	CP					
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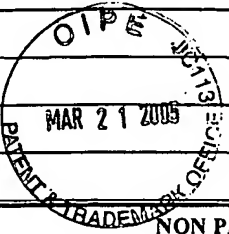
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LP ↓ V	AO	SHIN, JONGSHIN, ET AL., "A New Charge Pump Without Degradation in Threshold Voltage Due to Body Effect," IEEE Journal of Solid-State Circuits, Vol. 35, No. 8, August 2000, pp. 1227-1230.	
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